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(71) Applicant: **GLOBALWAFERS CO., LTD.** [CN/CN];
No. 8 Industrial East Road 2, Science-Based Industrial Park,
Hsinchu (TW).

(72) Inventors: **ZEPEDA, Salvador**; 501 Pearl Drive, St. Pe-
ters, Missouri 63376 (US). **SAMANTA, Gaurab**; 501 Pearl
Drive, St. Peters, Missouri 63376 (US).

(74) Agent: **SCHUTH, Richard, A.** et al.; Armstrong Teasdale
LLP, 7700 Forsyth Blvd., Suite 1800, St. Louis, Missouri
63105 (US).

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(54) Title: METHOD FOR TRANSFER OF A THIN LAYER OF SILICON

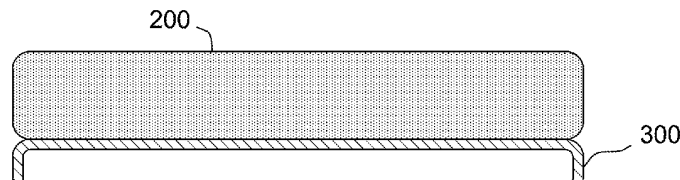


FIG. 1F

(57) Abstract: A method for preparing semiconductor on insulator structures comprises transferring a thin layer of silicon from a donor substrate onto a handle substrate.



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